AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A method comprising:

removing a material from a surface of a wafer by chemical mechanical polishing the wafer with a slurry comprising an oxidation agent for the material and a buffer; and

monitoring a signal representative of current required to rotate the wafer as a measure of a material removal endpoint,

wherein the buffer in the slurry is present in an amount sufficient to at least double a differential between a signal measured at a material removal start point and the material removal endpoint relative to a slurry without the buffer.

2. (Original) The method of Claim 1, further comprising:

buffering with a weak organic acid/salt pair.

3. (Original) The method of Claim 2, further comprising:

buffering with a weak organic acid/salt from the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.

4. (Previously Presented) A composition comprising:

a slurry for chemical mechanical polishing a metal material;

an oxidizing agent for the metal material;

an abrasive; and

a buffer present in an amount sufficient to at least double a differential between a signal measured at a material removal start point and the material removal endpoint relative to a slurry without the buffer;

wherein the composition is suitable for use in a chemical mechanical polish process.

5. (Original) The composition of Claim 4, wherein the oxidizing agent is hydrogen peroxide.

6. (Original) The composition of Claim 4, wherein the buffer is a weak organic acid/salt pair.

7. (Original) The composition of Claim 6, wherein the weak organic acid comprises one of the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.

8. (Previously Presented) The composition of Claim 4, wherein the metal material comprises one of the group consisting of tungsten and titanium nitride.

9. (Canceled)

10. (Original) The composition of Claim 4, wherein the abrasive comprises one of the group consisting of silica and alumina.

11. (Previously Presented) The composition of Claim 4, wherein the endpoint signal of the composition is enhanced over an endpoint signal of a composition comprising a slurry, an oxidizing agent, and an abrasive and without a buffer by at least a factor of two.

12. (Previously Presented) A kit comprising:

a slurry for chemical mechanical polishing a metal material;

an oxidizing agent for the metal material;

an abrasive; and

a buffer in an amount sufficient to at least double a differential between a signal measured at a material removal start point and the material removal endpoint relative to a slurry without the buffer,

wherein the slurry, the oxidizing agent, the abrasive, and the buffer are to be combined into a polish suitable for a chemical mechanical polish operation.

13. (Previously Presented) The kit of Claim 12, wherein the metal material comprises one of the group consisting of tungsten and tantalum nitride.

14. (Original) The kit of Claim 12, wherein the abrasive comprises one of the group consisting of silica or alumina.

15. (Original) The kit of Claim 12, wherein the buffer is an organic acid/salt pair.

16. (Original) The kit of Claim 15, wherein the organic acid comprises one of the group consisting of citric acid/potassium citrate, acetic acid/potassium acetate and ascorbic acid/potassium ascorbate.

17. (Previously Presented) The kit of Claim 12, wherein the endpoint signal of the polish is enhanced over the endpoint signal of a polish comprising a slurry, an oxidizing agent, and an abrasive and without a buffer by at least a factor of two.